

NEC
ELECTRON DEVICE

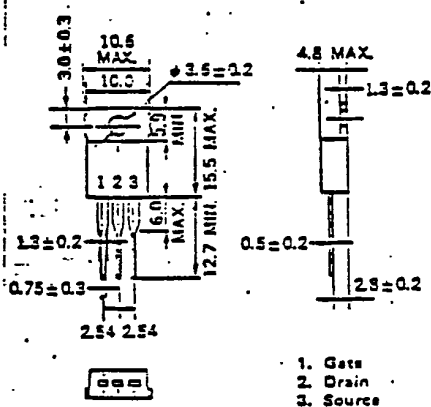
PRELIMINARY SPECIFICATION

MOS FIELD EFFECT TRANSISTOR

2SK854

**FAST SWITCHING
N-CHANNEL SILICON POWER MOS FET**

PACKAGE DIMENSIONS
(Unit: mm)

**Features**

Suitable for switching power supplies,
actuator controls and pulse circuits
Low $R_{DS(on)}$

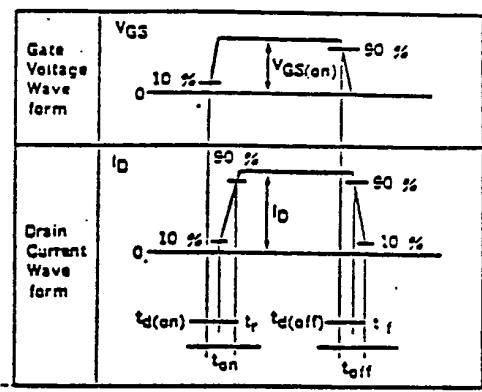
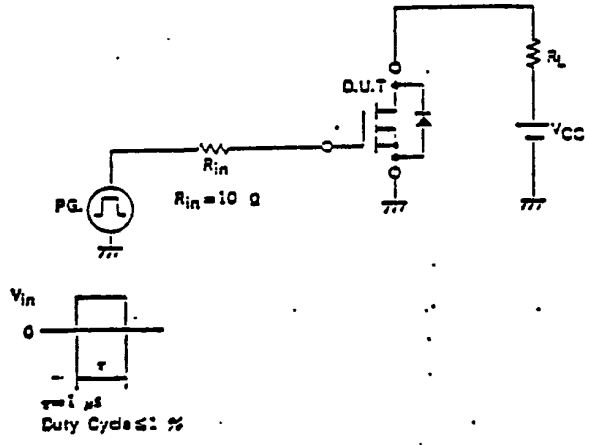
Absolute Maximum Ratings ($T_a=25^\circ\text{C}$)

Drain to Source Voltage	V_{DS}	450V
Gate to Source Voltage	V_{GS}	$\pm 20\text{V}$
Continuous Drain Current	$I_D(\text{DC})$	$\pm 5\text{A}$
Pulse Drain Current	$I_D(\text{pulse})$	$\pm 20\text{A}$
Total Power Dissipation	PT	1.5W
Total Power Dissipation	PT**	50W
Channel Temperature	T_{ch}	150 $^\circ\text{C}$
Storage Temperature	T_{stg}	-55 to 150 $^\circ\text{C}$

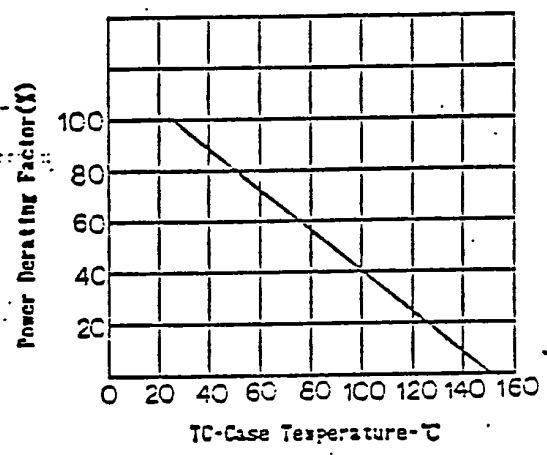
* $PW \leq 100 \mu\text{s}$, Duty Cycle $\leq 2\%$ ** $T_c=25^\circ\text{C}$ **Electrical Characteristics ($T_a=25^\circ\text{C}$)**

Characteristics	Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Drain Leakage Current	I_{DSS}			100	μA	$V_{DS}=450\text{V}, V_{GS}=0$
Gate to Source Leakage Current	I_{GSS}			± 100	nA	$V_{GS}=\pm 20\text{V}, V_{DS}=0$
Gate to Source Cutoff Voltage	$V_{GS}(\text{off})$	1.5		3.5	V	$V_{DS}=10\text{V}, I_D=1.0\text{mA}$
Forward Transfer Admittance	y_{fs}	2.5			S	$V_{DS}=10\text{V}, I_D=2.5\text{A}$
Drain to Source On-State Resistance	$R_{DS(on)}$			1.4	Ω	$V_{GS}=10\text{V}, I_D=2.5\text{A}$
Input Capacitance	C_{iss}		700		pF	$V_{DS}=10\text{V}, V_{GS}=0$
Output Capacitance	C_{oss}		175		pF	$V_{GS}=0$
Reverse Transfer Capacitance	C_{rss}		40		pF	$f=1.0\text{MHz}$
Turn-On Delay Time	$t_d(\text{on})$		10		ns	$I_D=2.5\text{A}$
Rise Time	t_r		15		ns	$V_{GS}(\text{on})=10\text{V}$
Turn-Off Delay Time	$t_d(\text{off})$		40		ns	$V_{CC}=150\text{V}$
Fall Time	t_f		15		ns	$R_L=60\Omega$

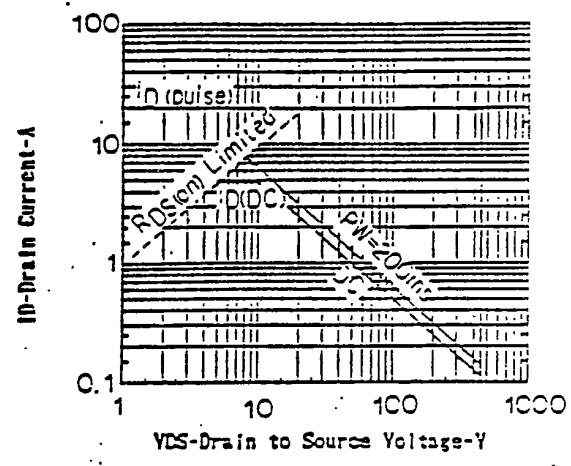
TURN-ON AND TURN-OFF TIME TEST CIRCUIT



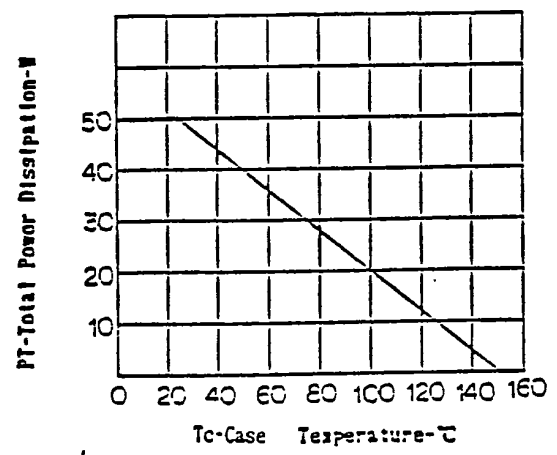
DERATING FACTOR OF FORWARD BIAS SAFE OPERATING AREA



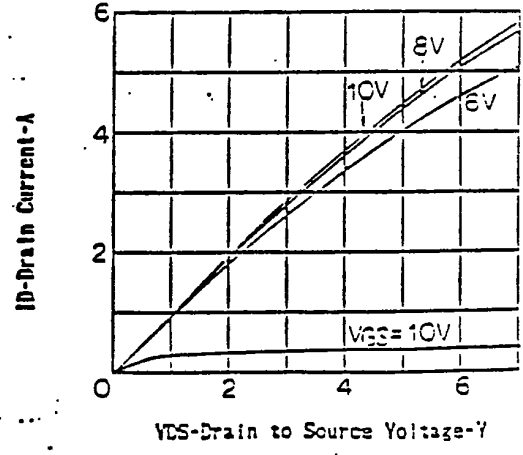
FORWARD BIAS SAFE OPERATING AREA

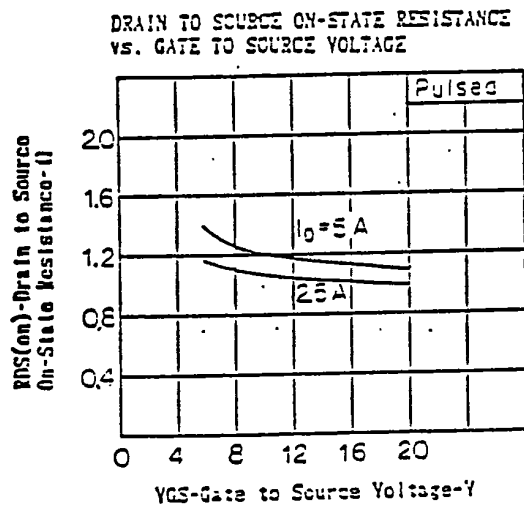
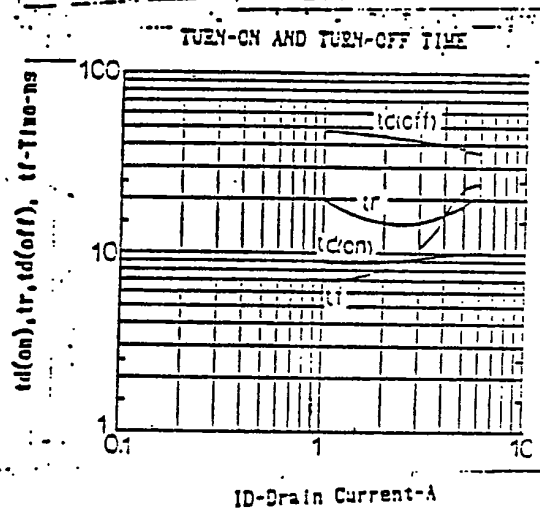
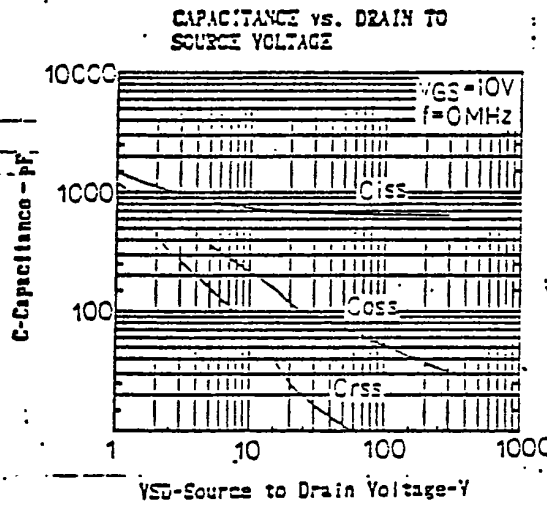
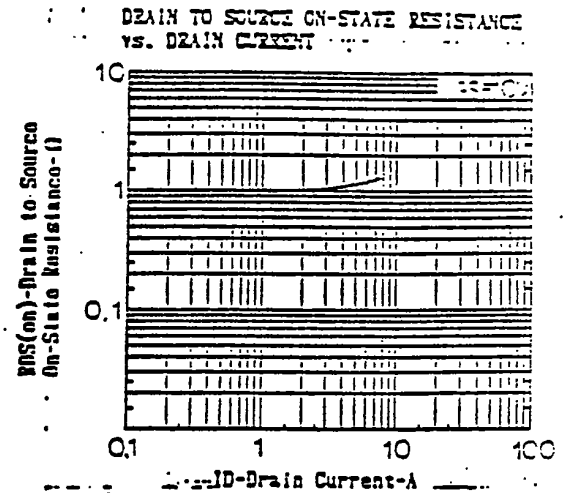
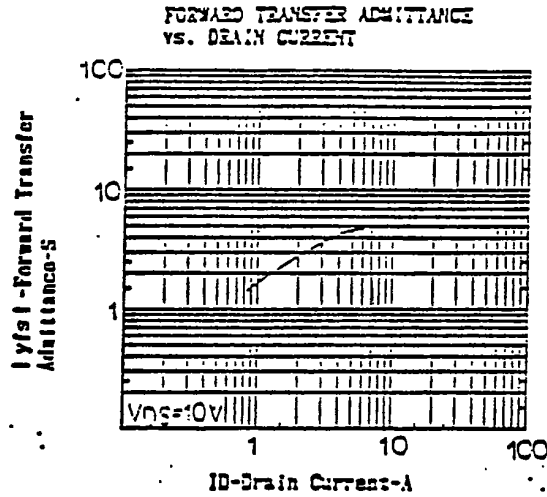


TOTAL POWER DISSIPATION vs. CASE TEMPERATURE



DRAIN CURRENT vs. DRAIN TO SOURCE VOLTAGE







LittleDiode supplies new, hard to find or obsolete electronic components and semiconductors all over the world.

With over two million different components listed you are sure to find the part you need.

Feel free to visit us today at our online store:

LittleDiode.com

Looking forward to providing you with the best possible service.